

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of the Claims:

Claim 1 (canceled)

1 Claim 2 (currently amended): A semiconductor laser,
2 comprising;
3 a semiconductor substrate;
4 a laser layer on said semiconductor substrate;
5 at least two waveguide ridges located at a distance from
6 said laser layer whereby electrical injection into said
7 laser layer is achieved through at least two of said
8 waveguide ridges, and
9 a first strip-shaped lattice structure comprising
10 alternating portions of conducting and non-conducting or
11 less conducting material, wherein said lattice structure is
12 located on the flat portions of the surface between said
13 ridges and at a distance from said laser layer above said
14 laser layer, and A semiconductor laser according to claim 1,
15 further comprising a second strip-shaped lattice structure
16 located lateral to the two outermost of said waveguide
17 ridges, wherein said lattice structure is located on the
18 flat portions of the surfaces lateral to said outermost
19 ridges and at a distance from said laser layer above said
20 laser layer.

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1 Claim 3 (currently amended): The semiconductor laser
2 according to ~~claim 1~~ claim 2, wherein said lattice structure
3 is located on a barrier or insulating layer wherein said
4 barrier defines the position of said lattice structure
5 relative to said laser layer.

1 Claim 4 (currently amended): The semiconductor laser
2 according to ~~claim 1~~ claim 2, wherein said lattice structure
3 comprises a metal.

1 Claim 5 (original): The semiconductor laser according to
2 claim 4, wherein said metal is chromium or a chromium alloy.

1 Claim 6 (currently amended): The semiconductor laser
2 according to ~~claim 1~~ claim 2, wherein said first
3 strip-shaped lattice structure is located adjacent to sides
4 of said waveguide ridges, and wherein the width and spacing
5 of said waveguide ridges are selected such that base points
6 of the sides of said waveguide ridges are located in a
7 peripheral region of radiation from an active zone of said
8 laser layer.

Claims 7-10 (canceled)